

# A Hybrid Dielectric-Semiconductor Metasurface for Efficient Second-Harmonic Generation

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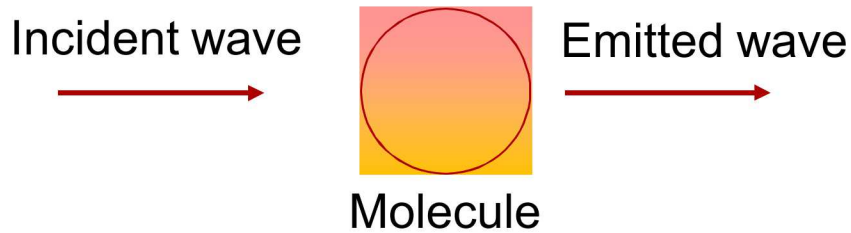
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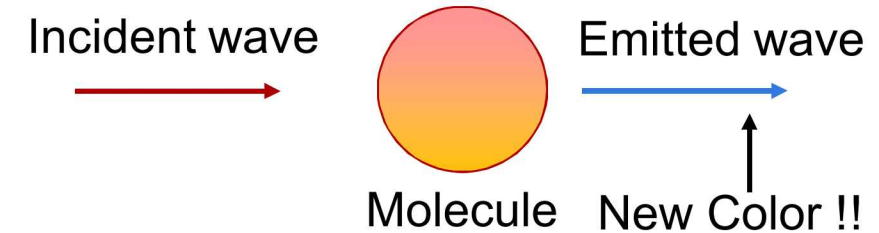
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# Nonlinear Optics : Second-Harmonic Generation (SHG)

Linear Optics



Nonlinear Optics



Dielectric polarization density  $\mathbf{P}(t)$   
– dipole moment per unit volume

$$\mathbf{P}(t) = \epsilon_0 (\chi^{(1)} \mathbf{E}(t) + \chi^{(2)} \mathbf{E}^2(t) + \chi^{(3)} \mathbf{E}^3(t) + \dots),$$

where the coefficients  $\chi^{(n)}$  are the  $n$ -th-order **susceptibilities** of the medium.

# Prominent On-Chip Approaches for SHG

## IST-Plasmonic Metasurface

### Ultrathin Second-Harmonic Metasurfaces with Record-High Nonlinear Optical Response

Jongwon Lee, Nishant Nookala, J. Sebastian Gomez-Diaz, Mykhailo Tymchenko, Frederic Demmerle, Gerhard Boehm, Markus-Christian Amann, Andrea Alù, and Mikhail A. Belkin\*

## All Dielectric Metasurface

### Resonantly Enhanced Second-Harmonic Generation Using III–V Semiconductor All-Dielectric Metasurfaces

Sheng Liu,<sup>\*,†</sup> Michael B. Sinclair,<sup>†</sup> Sina Saravi,<sup>§</sup> Gordon A. Keeler,<sup>†</sup> Yuanmu Yang,<sup>†,‡</sup> John Reno,<sup>†,‡</sup> Gregory M. Peake,<sup>†</sup> Frank Setzpfandt,<sup>§</sup> Isabelle Staude,<sup>§</sup> Thomas Pertsch,<sup>§</sup> and Igal Brener<sup>\*,†,‡</sup>

## Plasmonics

### Nonlinear plasmonics

Martti Kauranen<sup>1</sup> and Anatoly V. Zayats<sup>2</sup>

## ARTICLE

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OPEN

## Phased-array sources based on nonlinear metamaterial nanocavities

Omri Wolf<sup>1,2,\*</sup>, Salvatore Campione<sup>1,2,\*</sup>, Alexander Benz<sup>1,2</sup>, Arvind P. Ravikumar<sup>3</sup>, Sheng Liu<sup>1,2</sup>, Ting S. Luk<sup>1,2</sup>, Emil A. Kadlec<sup>2</sup>, Eric A. Shaner<sup>2</sup>, John F. Klem<sup>2</sup>, Michael B. Sinclair<sup>2</sup> & Igal Brener<sup>1,2</sup>

### Nonlinear Generation of Vector Beams From AlGaAs Nanoantennas

Rocio Camacho-Morales,<sup>†</sup> Mohsen Rahmani,<sup>†</sup> Sergey Kruk,<sup>†</sup> Lei Wang,<sup>†</sup> Lei Xu,<sup>†,||</sup> Daria A. Smirnova,<sup>†</sup> Alexander S. Solntsev,<sup>†</sup> Andrey Miroschnichenko,<sup>†</sup> Hark Hoe Tan,<sup>‡</sup> Fouad Karouta,<sup>‡</sup> Shagufta Naureen,<sup>‡</sup> Kaushal Vora,<sup>‡</sup> Luca Carletti,<sup>⊥</sup> Costantino De Angelis,<sup>⊥</sup> Chennupati Jagadish,<sup>‡</sup> Yuri S. Kivshar,<sup>†</sup> and Dragomir N. Neshev<sup>\*,†</sup>

### Efficient Nonlinear Metasurface Based on Nonplanar Plasmonic Nanocavities

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Max. Conversion factor ~ 16.8 mW/W<sup>2</sup>  
Max. Efficiency ~ 7 x 10<sup>-4</sup> at 15 kW/cm<sup>2</sup>

Max. Conversion factor ~ 2 x 10<sup>-5</sup> mW/W<sup>2</sup>  
Max. Efficiency ~ 10<sup>-4</sup> -10<sup>-5</sup> at ~ 5 GW/cm<sup>2</sup>

Max. Efficiency 6 x10<sup>-5</sup>  
at ~ 0.5 GW/cm<sup>2</sup>

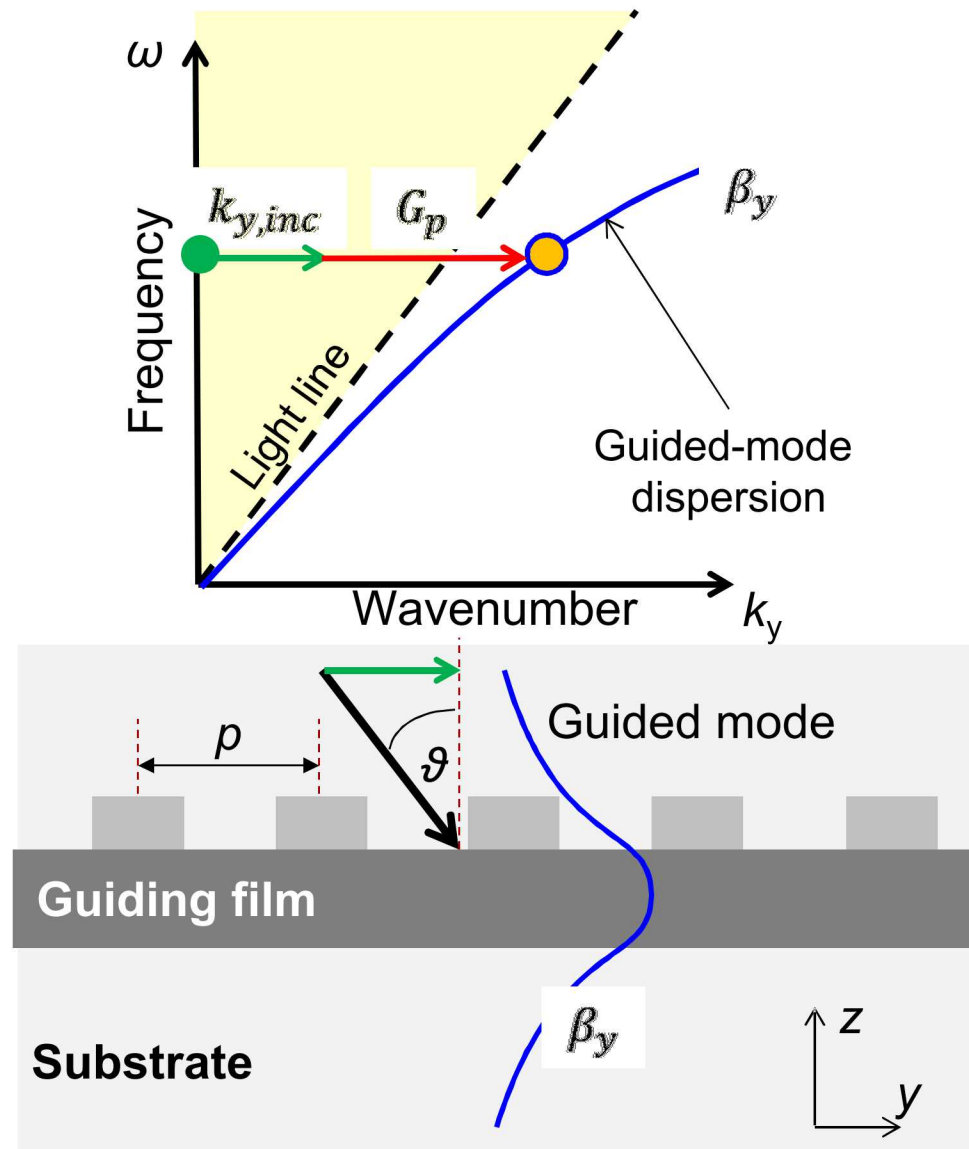
# Desired Properties for Nonlinear Metasurfaces

1. **High second-order nonlinear susceptibility** : IST in QWs
2. **Large field enhancement** : High Q Resonances
3. **Large damage threshold and low loss at all wavelengths**  
: Dielectric structures
4. **Large bandwidth** : Require new type of resonances as  
high Q and bandwidth work in  
opposite directions
5. **Practical aspects** : Easy to fabricate, monolithically integrable,  
Dual mode operation ( reflection/transmission)

Can we design a hybrid approach that has all these properties ?

Yes, using a hybrid approach of ***coupling leaky mode resonances*** in dielectric structures to ***ISTs*** in QWs

# What is a Leaky Mode Resonance ?



Incident transverse wavenumber

$$k_{y,inc} = \frac{\omega}{c} \sin \vartheta$$

+

Lattice transverse momentum

$$G_p = \frac{2\pi}{p} m, \text{ where } m = \pm 1, \pm 2, \pm 3, \dots$$

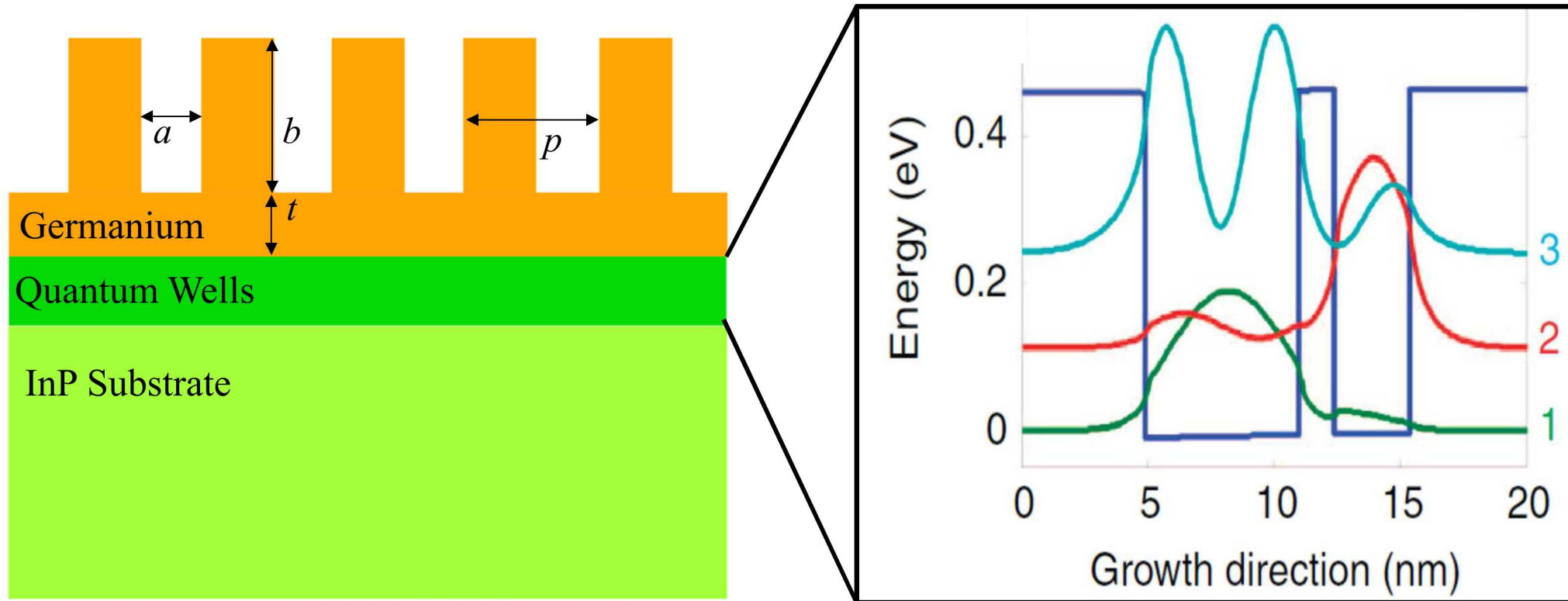
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Plane wave excitation of a  
Leaky Mode Resonance

$$|k_{y,inc} + G_p| = \tilde{\beta}_y$$

For small perturbation,  $\tilde{\beta}_y \sim \beta_y$

# Dielectric-Semiconductor Hybrid Structure for SHG



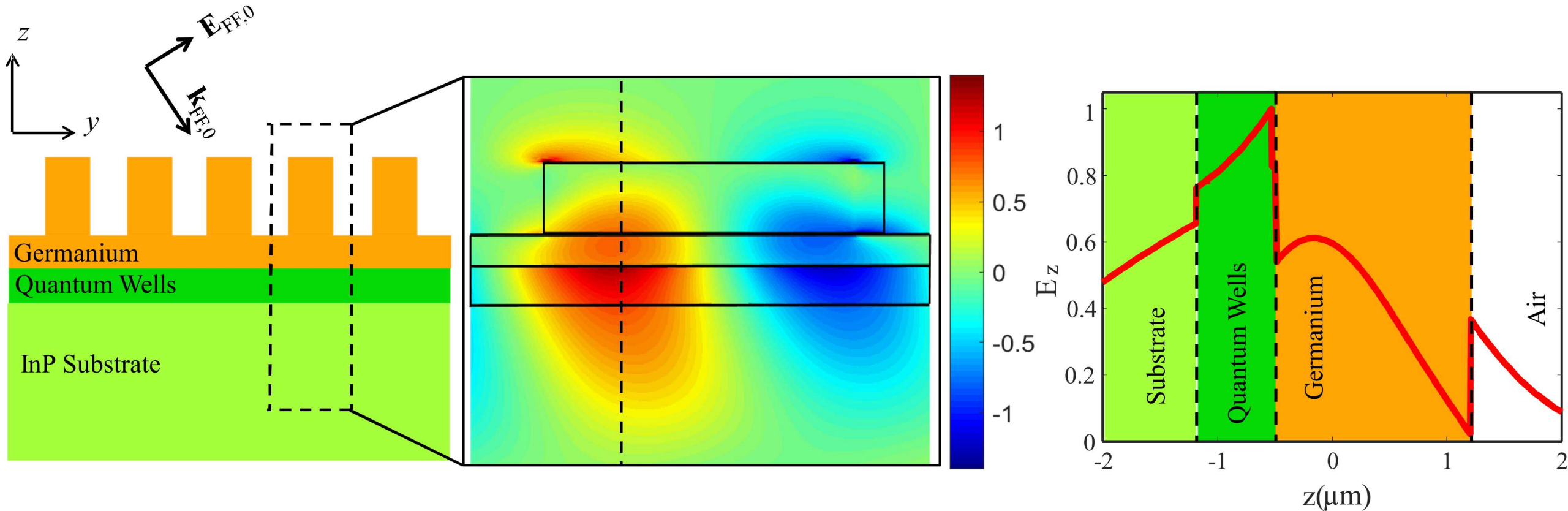
$a=1070\text{nm}$  ,  $b=1200\text{nm}$  ,  $t=500\text{nm}$   
 $p=3150, 3250, 3350\text{ nm}$

InGaAs QWs with AlInAs barriers

Ref. : O. Wolf et. al., Nature Comm. 6 (2015)

The thickness of the InGaAs QWs is optimized to have transitions at 10 microns and 5 microns. The geometrical parameters of the grating structure is designed for these wavelengths.

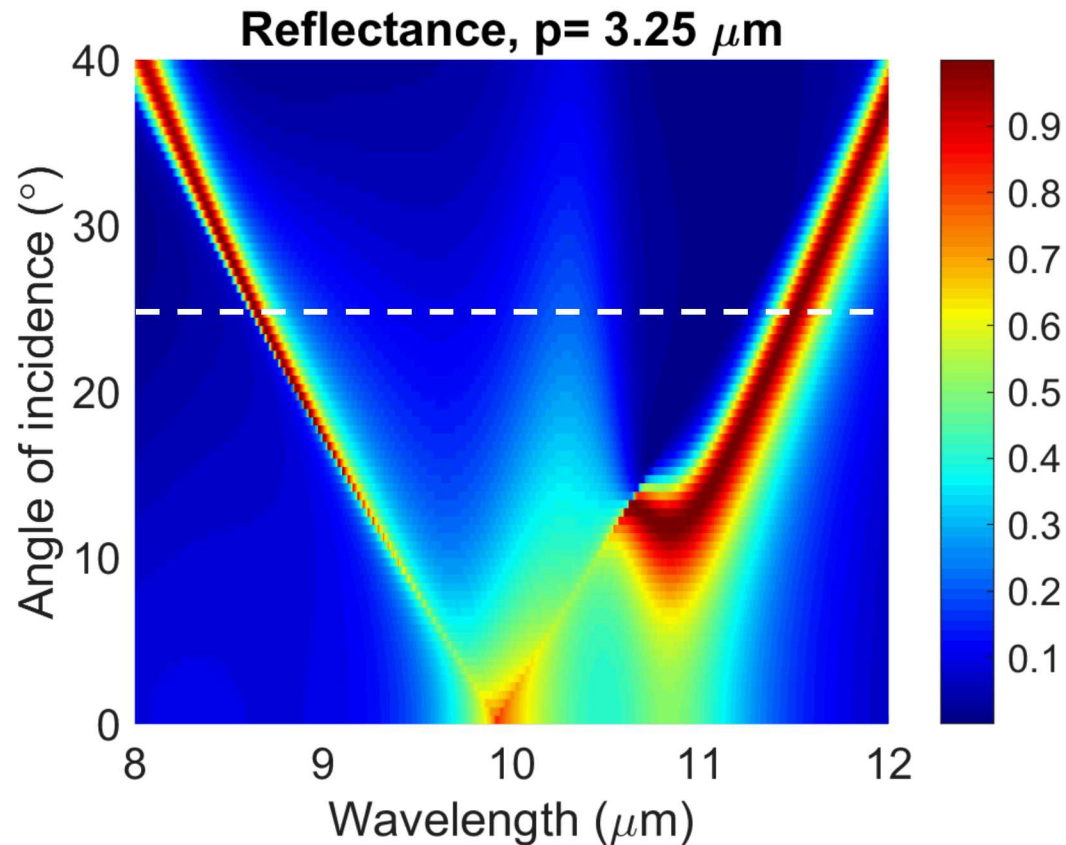
# Leaky Mode Resonance Coupled to IST



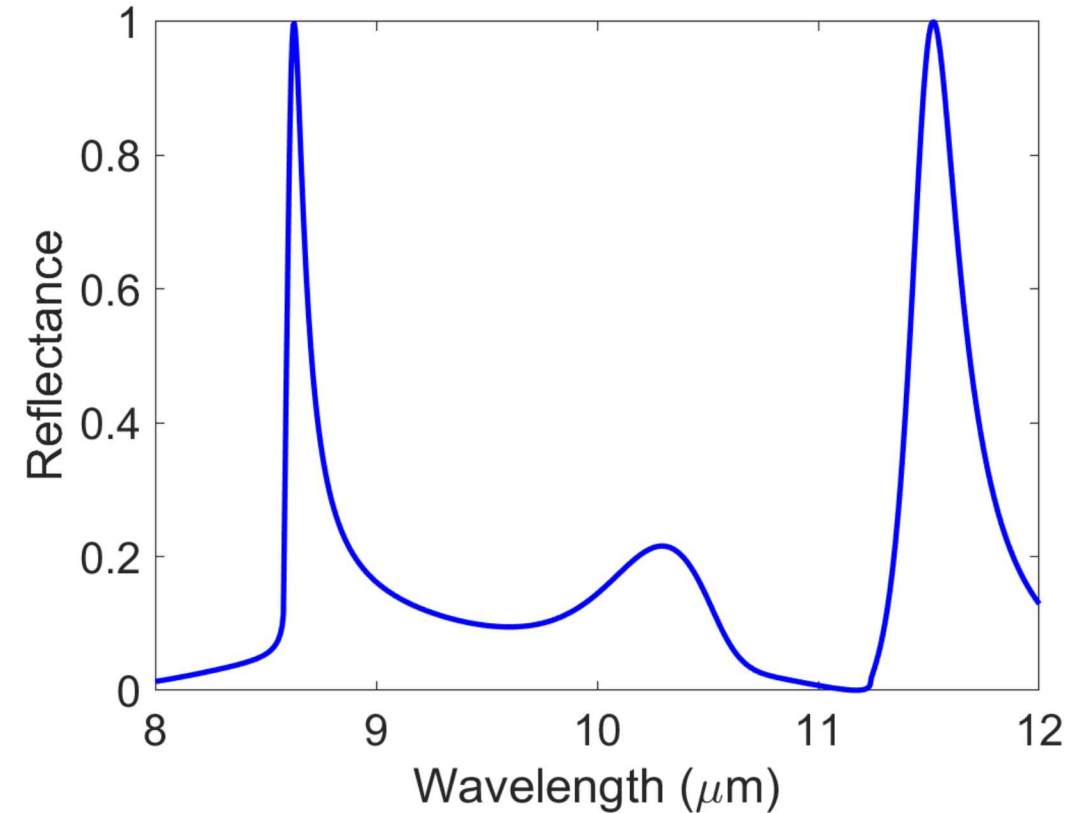
The pump wavelength (fundamental frequency, FF) is at 10 microns. The evanescent fields of the leaky mode resonance drives the ISTs in the QWs.

# Leaky Mode Resonances : High Q and Large Bandwidth

Linear Simulations ( Ignoring IST absorption)



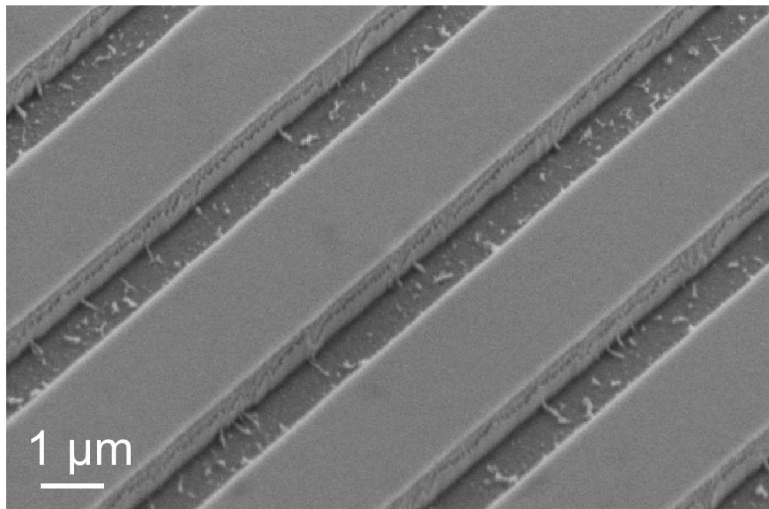
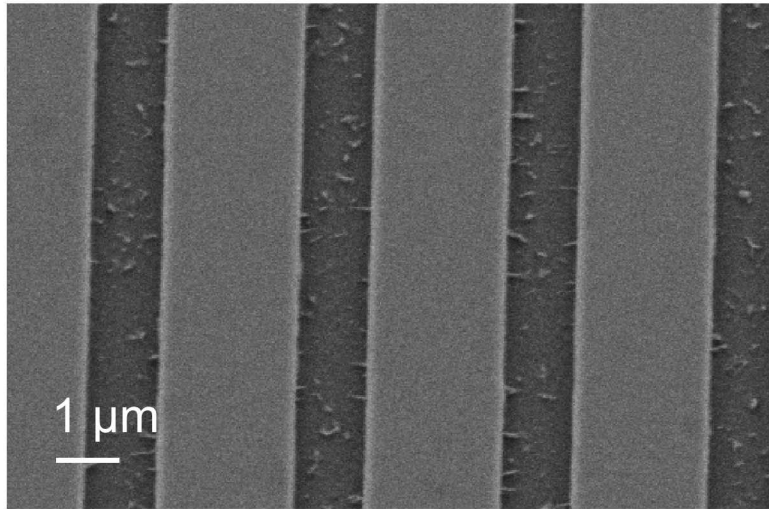
Cross Section of Reflectance ( white dashed line)



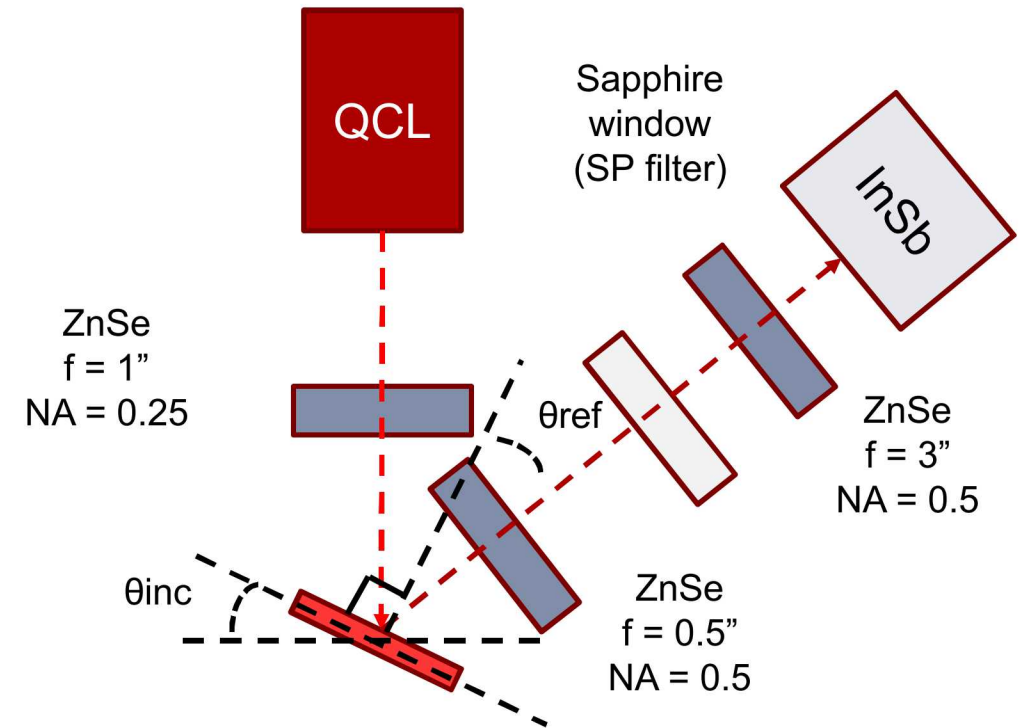
The leaky mode resonances have high Q with Fano features and can exist for all wavelengths between 8-12 microns

# Device Fabrication and Experimental Setup

Scanning Electron Micrographs

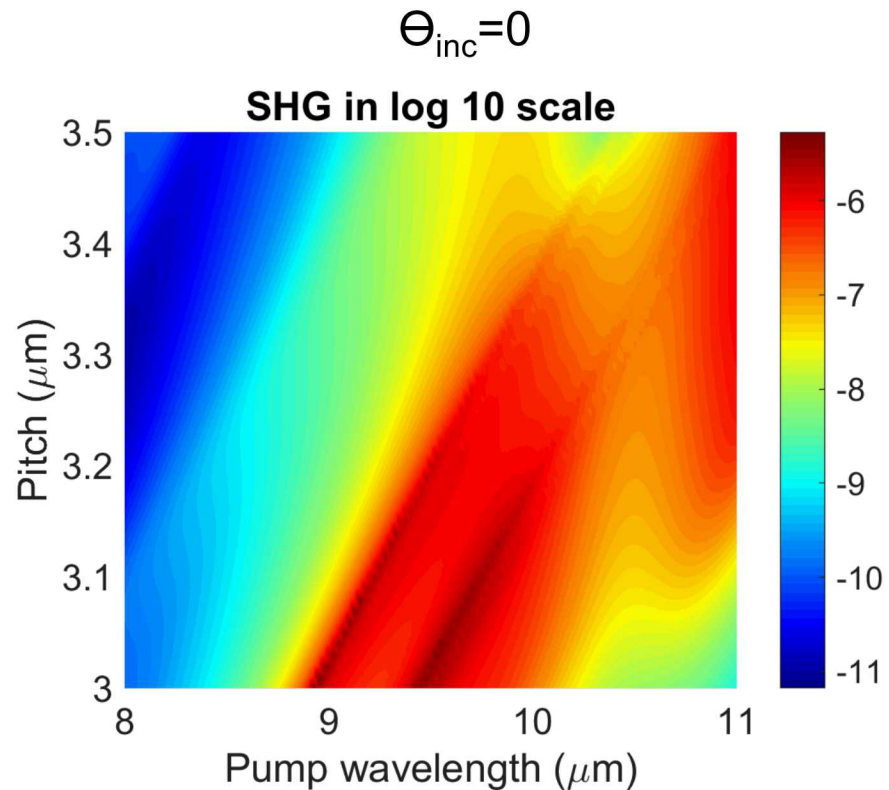


Experimental Setup



Normal incidence measurements  
correspond to  $\Theta_{\text{inc}} = 0$

# Experimental Data and Comparison to Simulations

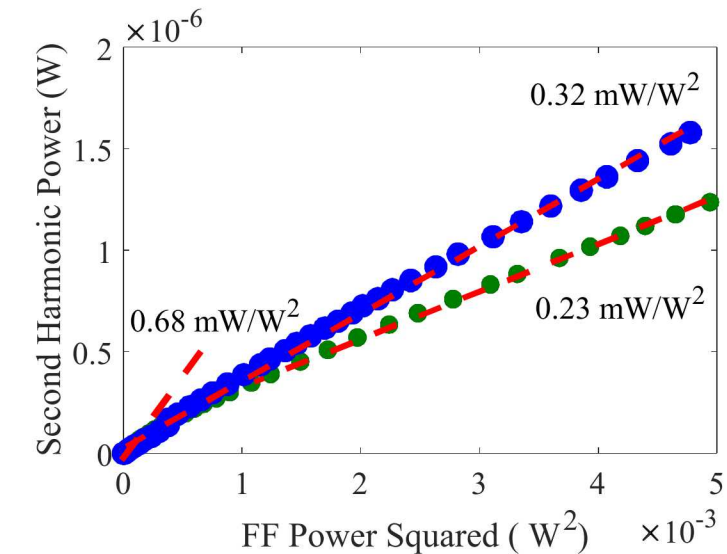
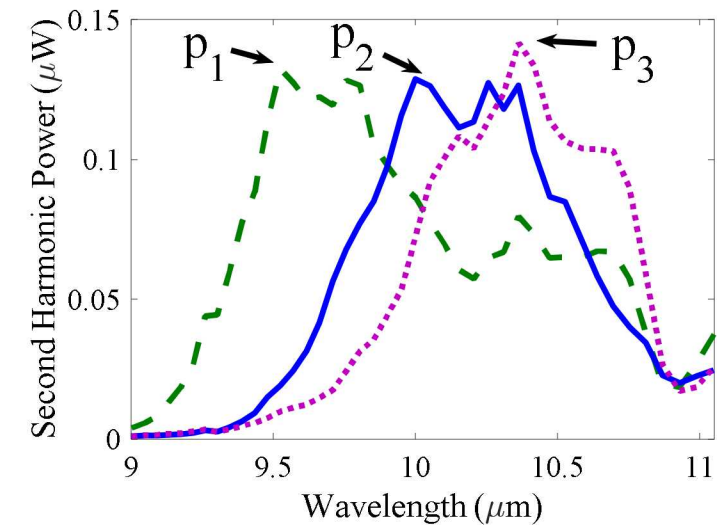


As predicted by simulations, the peak of SHG red shifts as period increases

Maximum SHG conversion factor =  $0.68 \text{ mW/W}^2$

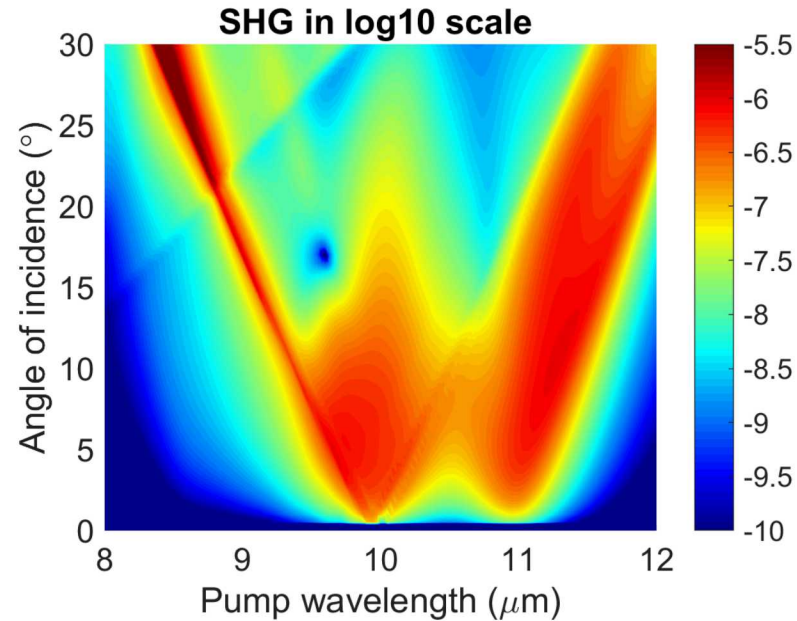
Max. SHG efficiency  $\sim 3 \times 10^{-5}$  at  $15 \text{ kW/cm}^2$

$\Theta_{\text{inc}}=0$  and  $p = 3150, 3250$  and  $3350 \text{ nm}$



# Experimental Data and Comparison to Simulations

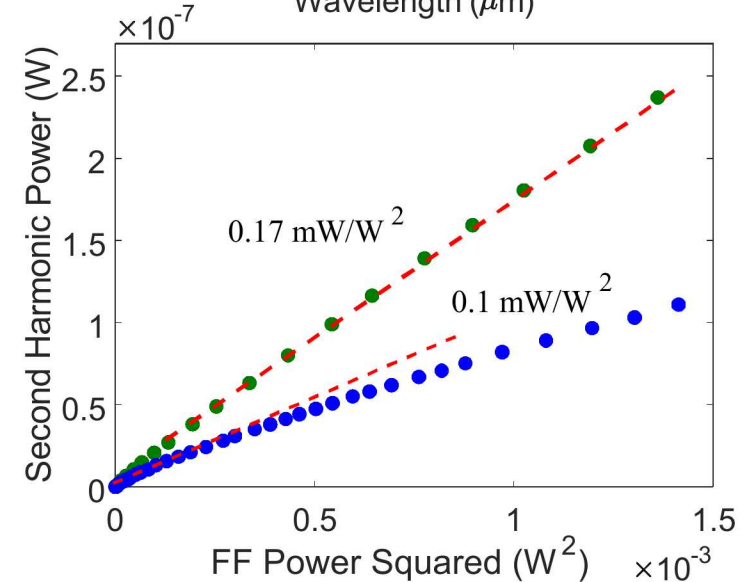
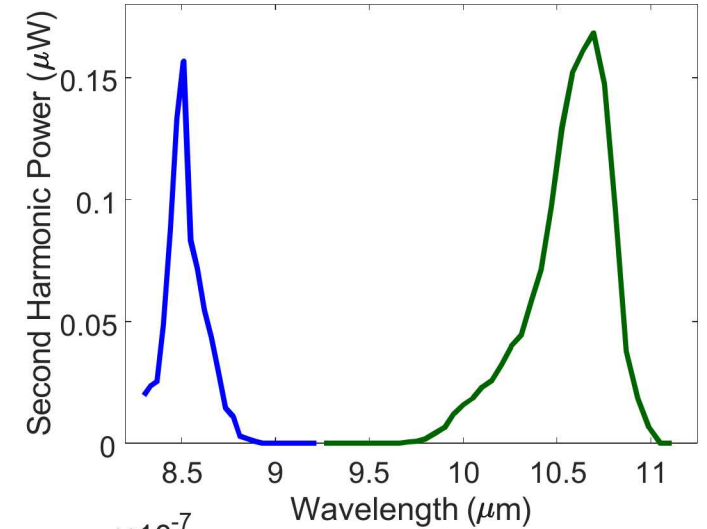
$p = 3250 \text{ nm}$



As predicted by simulations, at  $\Theta_{\text{inc}}=25$  degrees, two peaks of SHG are observed at 8.5 (narrower) and  $\sim 10.75$  microns (broader).

Maximum SHG conversion factor =  $0.17 \text{ mW/W}^2$   
Max. SHG efficiency  $\sim 1.8 \times 10^{-5}$  at  $\sim 10 \text{ kW/cm}^2$

$\Theta_{\text{inc}}=25$  degrees and  $p = 3250 \text{ nm}$



# Summary

1. We have demonstrated a hybrid approach for realizing a dielectric-semiconductor planar nanostructure for high efficiency SHG with increased bandwidth.
2. Using our devices, we demonstrate SHG at pump wavelengths ranging from  $\sim 8.5$ -11 microns. The maximum observed SHG conversion factor is  $0.68 \text{ mW/W}^2$  and maximum conversion efficiency observed is  $\sim 3 \times 10^{-5}$  at  $15 \text{ kW/cm}^2$  pump power.
3. In addition to fundamental advantages, the approach also has practical advantages such as wavelength scalability, monolithic integrability, and ease of fabrication. The devices can also be fabricated using optical lithography.
4. The results here demonstrate a proof-of-concept and there is further scope of improvement of SHG efficiency by optimizing various parameters such as the dielectric medium of the grating, geometrical parameters, semiconductor heterostructure etc.